

k-resolved ultrafast light-induced band renormalization in monolayer WS₂ on graphene

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Abstract

Understanding and controlling the electronic properties of two-dimensional materials is crucial for their potential applications in nano- and optoelectronics. Monolayer transition metal dichalcogenides such as WS₂ have garnered significant interest due to their strong light-matter interaction and extreme sensitivity of the band structure to the presence of photogenerated electron-hole pairs. In this study, we investigate the transient electronic structure of monolayer WS₂ on a graphene substrate after resonant excitation of the A-exciton using time- and angle-resolved photoemission spectroscopy. We observe a pronounced band structure renormalization including a substantial reduction of the transient band gap that is in good quantitative agreement with our *ab initio* theory that reveals the importance of both intrinsic WS₂ and extrinsic substrate contributions to the transient band structure of monolayer WS₂. Our findings not only deepen the fundamental understanding of band structure dynamics in two-dimensional materials but also offer valuable insights for the development of novel electronic and optoelectronic devices based on monolayer TMDs and their heterostructures with graphene.

The size of the band gap of a semiconductor is the essential parameter that determines its optical and electronic properties with crucial importance for light absorption in solar cells and photodetectors as well as the performance of transistors and other electronic devices. In two-dimensional (2D) semiconductors such as monolayer transition metal dichalcogenides (TMDs), confinement and reduced screening give rise to strong electronic correlations that modify the size of the quasiparticle gap and lead to the formation of excitons with large binding energies that dominate the optical response. Controlling the band gap of 2D semiconductors is highly relevant for the development of next generation optoelectronic devices. This is commonly done by tailoring the dielectric screening. At equilibrium, this has been achieved by embedding 2D semiconductors in van der Waals (vdW) heterostructures^{1,2} or by changing the carrier density with a gate voltage³. Out of equilibrium, photodoping with femtosecond laser pulses has been used to modify the screening dynamically, which offers the possibility to control the size of the band gap on femtosecond time scales⁴⁻¹².

Ab initio theory predicts that the band shifts caused by the presence of excited carriers are non-rigid with a pronounced momentum dependence^{13,14}. To date, however, experiments have mainly probed the transient size of the direct gap at the K-point. A possible momentum dependence of the transient gap remains unexplored.

Here, we use time- and angle-resolved photoemission spectroscopy (trARPES) to probe the transient band structure of a 2D semiconductor over the whole Brillouin zone. For this purpose, we use monolayer WS₂ on a graphene/SiC(0001) substrate that we excite at resonance to the A-exciton at $\hbar\omega_{pump} = 2$ eV. We extract the size of the direct quasiparticle gap at the K-point as well as the momentum-resolved valence band (VB) shift as a function of time. The direct gap is found to shrink by $\Delta E \sim 140$ meV for a fluence of 1.5 mJ cm^{-2} . Within the experimental error bars, the transient VB shift is found to be rigid between Γ and K with a fluence-dependent amplitude ranging from $\Delta E \sim 100$ meV to $\Delta E \sim 170$ meV for fluences between 0.7 mJ cm^{-2} and 1.5 mJ cm^{-2} . Our trARPES results further provide access to the transient carrier distribution and temperature that serve as input parameters

for advanced *ab initio* calculations that include Hartree and GW contributions of WS₂ as well as GdW contributions of the graphene substrate. The calculations quantitatively reproduce the experimentally observed shifts. In addition, our theory allows us to disentangle the relevance of the individual contributions and to determine the momentum dependence of the band shifts.

The detailed microscopic understanding gained in this work provides important information for the design of next generation optoelectronic devices.

Sample growth: 6H-SiC substrates were H-etched to remove scratches and subsequently graphitized in Ar atmosphere. The resulting carbon monolayer with $(6\sqrt{3} \times 6\sqrt{3})$ R 30° structure was decoupled from the SiC substrate by H-intercalation, yielding quasi-freestanding monolayer graphene on H-terminated SiC(0001)¹⁵. WS₂ was then grown by chemical vapor deposition from solid WO₃ and S precursors¹⁶. WS₂ was found to grow in the shape of triangular islands with side lengths in the range of 300 – 700 nm with twist angles of either 0° or 30° with respect to the graphene layer¹².

trARPES: The setup was based on a commercial titanium sapphire amplifier (Astrella, Coherent) with a central wavelength of 800 nm, a repetition rate of 1 kHz, a pulse duration of 35 fs, and a pulse energy of 7 mJ. 5 mJ were used to seed a commercial optical parametric amplifier (Topas Twins, Light Conversion) the signal output of which was frequency doubled, yielding 2 eV pump pulses resonant with the A-exciton of monolayer WS₂. The remaining 2 mJ of output energy were frequency doubled and focused onto an argon gas jet for high harmonic generation. A single harmonic at 21.7 eV photon energy was selected with a grating monochromator yielding extreme ultraviolet (XUV) probe pulses that were used to eject photoelectrons from the sample. The photoelectrons were dispersed according to their kinetic energy and emission angle by a hemispherical analyzer (Phoibos 100, SPECS), yielding two-dimensional snapshots of the occupied part of the band structure in momentum space. The probe spot diameter was $\sim 250 \mu\text{m}$ on the sample, covering many different WS₂ islands. Nevertheless, 0° and 30° WS₂ islands were easily distinguished based on the dispersion of

their band structure in momentum space. The energy and temporal resolutions for the measurements presented in the present publication were ~ 200 meV and 160 fs, respectively.

Theory: We combine non-equilibrium Green functions with *ab initio* calculations of the ground state properties to compute the influence of photoexcited electron-hole pairs on the transient electronic structure of monolayer WS₂ on a graphene/SiC substrate across the whole Brillouin zone. Electrons and holes are assumed to follow a quasi-thermal distribution with one common elevated temperature. The influence of excited carriers inside the WS₂ layer is treated explicitly in the GW self-energy. The contribution of excited carriers inside the graphene layer enters via a macroscopic dielectric function. We consider both Hartree and static as well as dynamical exchange renormalizations. Further details are provided in the Supporting Information (SI).

Figure 1a shows the band structure of the WS₂-graphene sample measured along the Γ K-direction of the 0° WS₂ islands at negative pump-probe delay before the arrival of the pump pulse. Dashed white lines are theoretical band structures from¹⁷ for monolayer WS₂ and from¹⁸ for monolayer graphene that have been shifted in energy to account for the experimentally observed doping and equilibrium gap size. The dashed gray line indicates the dispersion of the 30° WS₂ islands. The orange arrow highlights the direct electronic transition triggered by photoexcitation at $\hbar\omega_{\text{pump}} = 2$ eV. Figure 1b shows the pump-induced changes of the photocurrent at a pump-probe delay of $t = 250$ fs for a pump fluence of $F = 1.5$ mJ cm⁻². Red and blue indicate gain and loss, respectively, with respect to the unperturbed photocurrent in Fig. 1a. The pump-probe signal exhibits three main features: (1) The minimum of the WS₂ conduction band (CB) at K_{WS₂} gets populated by the pump pulse. (2) The WS₂ VB exhibits a loss at its equilibrium position and a gain above, indicative of a transient up-shift. (3) The Dirac cone of graphene shows a loss of photoelectrons below and a gain of photoelectrons above the Fermi level, suggestive of a hot Fermi-Dirac distribution.

In order to extract the transient band gap at K_{WS₂} and the momentum-resolved VB shift,

we proceed as follows: we extract energy distribution curves (EDCs) at different momenta that we fit with an appropriate number of Gaussian peaks and a Shirley background to determine the transient binding energy of the WS₂ VB and CB and the Dirac cone of graphene. Further details are provided in the SI. The transient peak positions for the WS₂ CB and VB at K_{WS₂} are shown in Figs. 2a and b, respectively. The transient band gap obtained by subtracting the binding energy of the WS₂ VB in Fig. 2b from the binding energy of the WS₂ CB in Fig. 2a is shown in Figure 2c together with an exponential fit (see SI). The band gap is found to decrease by $\Delta E_{\text{gap}} = 140 \pm 20$ meV with a lifetime of $\tau = 0.9 \pm 0.2$ ps in good agreement with our own previous results⁹ and slightly lower than typical experimental^{4,6,8} and theoretical values^{19–22} reported in literature for similar samples. Possible reasons for this minor discrepancy might be related to the use of different substrates and the difficulty to estimate the density of photoexcited electron-hole pairs in the experiment (see below). Figure 2d shows the transient binding energy of the Dirac cone together with an exponential fit (see SI). The Dirac cone is found to shift down by $\Delta E = 90 \pm 10$ meV with a lifetime of $\tau = 0.6 \pm 0.1$ ps. The momentum-resolved shift of the WS₂ VB is shown in Fig. 2e for a pump-probe delay of $t_{\text{max}} \sim 500$ fs, where the VB shift at K_{WS₂} reaches its maximum, for three different fluences. Within the error bars, the observed VB shift is found to be momentum-independent with amplitudes of $\Delta E = 100 \pm 10$ meV, $\Delta E = 140 \pm 10$ meV, and $\Delta E = 170 \pm 10$ meV for fluences of $F = 0.7$ mJ cm⁻², $F = 1.0$ mJ cm⁻², and $F = 1.5$ mJ cm⁻², respectively. This is similar to the previously observed rigid band shift for monolayer WS₂ resting on different substrates² and consistent with previous predictions of *ab initio* theory for photoexcited samples^{13,14}.

Next, we determine the non-equilibrium carrier distribution of the WS₂-graphene sample at the pump-probe delay that corresponds to the momentum-resolved WS₂ VB shift shown in Fig. 2e to provide input for subsequent theory. Figure 3a shows the photocurrent integrated over the three areas marked by colored boxes in Fig. 1b as a function of pump-probe delay together with exponential fits. The Dirac cone of graphene shows a short-lived gain (red,

$\tau = 300 \pm 30$ fs) and a long-lived loss (blue, $\tau = 2.10 \pm 0.03$ ps). The lifetime of the electrons at the bottom of the WS₂ CB (yellow) is found to be $\tau = 950 \pm 70$ fs. Figure 3b shows the energy-resolved population of the Dirac cone, obtained by integrating the photocurrent over the momentum range indicated by the red scale bar in Fig. 1a, for two different time delays together with Fermi-Dirac fits (see SI). The resulting electronic temperature and chemical potential are shown in Figs. 3c and d, respectively. The electronic temperature reaches a peak value of $T_{e,\max} = 1900 \pm 100$ K and cools down with an exponential lifetime of $\tau = 760 \pm 60$ fs. From the electronic temperature and the chemical potential, we calculate the carrier concentration inside the Dirac cone as explained in detail in the SI. The result is shown in Fig. 3e as a function of pump-probe delay. We find that the carrier concentration inside the Dirac cone transiently decreases by $(5.7 \pm 1.2) \times 10^{12}$ cm⁻².

The observations in Figs. 2 and 3 have been previously attributed to ultrafast charge separation in WS₂-graphene heterostructures^{9,12,23}. Photoexcitation at resonance to the A-exciton of WS₂ is followed by rapid hole transfer into the graphene layer, resulting in a charge-separated transient state with a lifetime of ~ 1 ps. For a pump-probe delay of $t \sim 500$ fs, where the VB shift at K_{WS₂} reaches its maximum, we find the following carrier distribution in our WS₂-graphene sample: $\sim 3.4 \times 10^{12}$ cm⁻² holes are transferred from WS₂ to graphene, while $\sim 70\%$ of the photoexcited electrons remain in the WS₂ layer. The electrons inside the Dirac cone exhibit an elevated electronic temperature of $T_e \sim 1400$ K. The values for all fluences investigated in the present work are summarized in Table 1.

In Table 2 we present our estimates for the total density of photo-generated electron-hole pairs $n_{e,h}^{\text{WS}_2}$ for the three pump fluences employed in the experiment. This quantity is difficult to estimate as the absorption of 2D TMDs is highly non-linear due to Pauli blocking and many-body-effects¹⁴. According to¹⁴, $n_{e,h}^{\text{WS}_2}$ for hBN-encapsulated WS₂ is predicted to saturate around 0.5×10^{14} cm⁻² for fluences ≥ 0.5 mJ cm⁻². A lower limit for $n_{e,h}^{\text{WS}_2}$ is given by the maximum number of holes that are found to be transferred into the graphene layer during ultrafast charge separation.

Table 1: time delay t_{\max} , where WS₂ VB shift at K reaches its maximum; hole density inside Dirac cone $n_h^{gr}(t = t_{\max})$; electronic temperature of carriers inside Dirac cone $T_e(t = t_{\max})$.

pump fluence	t_{\max}	n_h^{gr}	T_e
0.7 mJ cm ⁻²	450 fs	7.9×10^{12} cm ⁻²	1000 K
1.0 mJ cm ⁻²	490 fs	8.8×10^{12} cm ⁻²	1300 K
1.5 mJ cm ⁻²	520 fs	10.4×10^{12} cm ⁻²	1400 K

Table 2: estimated upper and lower bound for the density of photo-generated electron-hole pairs for different fluences.

pump fluence	$n_{e,h}^{WS_2}$ upper limit	$n_{e,h}^{WS_2}$ lower limit
0.7 mJ cm ⁻²	5×10^{13} cm ⁻²	2×10^{12} cm ⁻²
1.0 mJ cm ⁻²	5×10^{13} cm ⁻²	3×10^{12} cm ⁻²
1.5 mJ cm ⁻²	5×10^{13} cm ⁻²	6×10^{12} cm ⁻²

The parameters in Tables 1 and 2 now serve as input for *ab initio* calculations of the transient band gap renormalization and WS₂ VB shift. At equilibrium, the graphene layer is found to be hole-doped with the Fermi level at -300 meV below the Dirac point (see Fig. 1a) corresponding to a hole concentration of $n_h^{gr,0} = 7 \times 10^{12}$ cm⁻². First, we correct the band structure of freestanding monolayer WS₂ by adding static GdW corrections due to screening from the graphene/SiC substrate. Next, we compute the transient changes of the WS₂ band structure due to screening from the photoexcited electron-hole pairs. For this purpose we assume initial photoexcited electron and hole densities in the range between $n_{e,h}^{WS_2} = 1 \times 10^{12}$ cm⁻² and $n_{e,h}^{WS_2} = 7 \times 10^{13}$ cm⁻² corresponding to the estimates provided in Table 2. Further, 90% of the photoexcited holes are assumed to be transferred into the graphene layer²⁴. For a WS₂ coverage of the graphene/SiC substrate of 50%¹² this corresponds to a hole density of $n_h^{gr} = n_h^{gr,0} + 0.5 \times 0.9 \times n_{e,h}^{WS_2}$ inside the graphene layer. Finally, we assume that all carriers have one common electronic temperature in the range between $T = 1000$ K and $T = 1400$ K (see Table 1) irrespective of their nature (electron or hole) and their location (WS₂ or graphene). Further details about the computational methods are presented in the SI. The results for the size of the transient momentum-resolved gap and VB shift at $T = 1500$ K are shown in Figs. 4a and b, respectively. We find that the direct WS₂ band gap at K_{WS_2} reduces by ~ 11 meV (~ 163 meV) for an electron density of

$n_e^{\text{WS}_2} = 1 \times 10^{12} \text{ cm}^{-2}$ ($7 \times 10^{13} \text{ cm}^{-2}$) with a k-dependent variation of $\sim 13 \text{ meV}$ ($\sim 46 \text{ meV}$). The VB shift is found to vary between mean values of $\sim 2 \text{ meV}$ and $\sim 70 \text{ meV}$ in the electron density range from $n_e^{\text{WS}_2} = 1 \times 10^{12} \text{ cm}^{-2}$ to $7 \times 10^{13} \text{ cm}^{-2}$ with a k-dependent variation between $\sim 6 \text{ meV}$ and $\sim 35 \text{ meV}$. Results for $T = 1000 \text{ K}$ are shown in the SI in SFig. 7. Note that the calculations do not take into account capacitor-like charging shifts that occur in the transient charge-separated state. For direct comparison between theory and experiment we subtract the charging shift from the experimental data points measured for a fluence of 1.5 mJ cm^{-2} as described in detail in the SI and include them as grey dots in Figs. 4a and b.

We find that the experimental data points are well reproduced by our calculations for an electron density of $n_e^{\text{WS}_2} = 5 \times 10^{13} \text{ cm}^{-2}$ corresponding to the upper limit of the estimated electron-hole pair density. The experimental error bars, however, are too large to allow for an experimental verification of the theoretically predicted k-dependence of the transient band structure changes. In contrast to experiment, our theory allows us to disentangle various different contributions to the transient band structure changes. Based on additional data provided in the SI we conclude that (i) free-standing monolayer WS_2 exhibits a VB shift that is roughly constant between Γ and K_{WS_2} but steeply increases at K_{WS_2} (SFig. 8). This cannot be reconciled with our experimental data in Fig. 2e. (ii) WS_2 GW contributions result in a k-dependent WS_2 VB shift with three minima along the ΓK direction (SFig. 9). The average amplitudes, however, are smaller than observed in experiment. (iii) For quantitative agreement with experiment additional graphene GdW contributions due to ultrafast hole transfer from WS_2 to graphene need to be considered (SFig. 10). These yield a WS_2 VB shift that is constant for the biggest part of the ΓK direction with a minimum at K_{WS_2} that appears at high carrier densities. We would like to stress that holes located in the WS_2 monolayer itself cause much stronger renormalizations than holes located in the relatively remote graphene layer (SFig. 11). (iv) WS_2 Hartree contributions are found to be negligible with WS_2 VB shifts below 1 meV (SFig. 12).

In summary, we showed that WS_2 on graphene exhibits a strong light-induced band structure renormalization that is well reproduced by our *ab initio* theory including Hartree and GW contributions of WS_2 as well as GdW contributions of the graphene substrate. The experimental error bars, however, are too large to allow for an experimental verification of the theoretically predicted k-dependence of the transient band structure changes. The microscopic insights gained in the present work may guide the development of future optoelectronic devices based on monolayer TMDs and their heterostructures with graphene.

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Supporting Information Available

The Supporting Information contains details about the data analysis and the theoretical model.

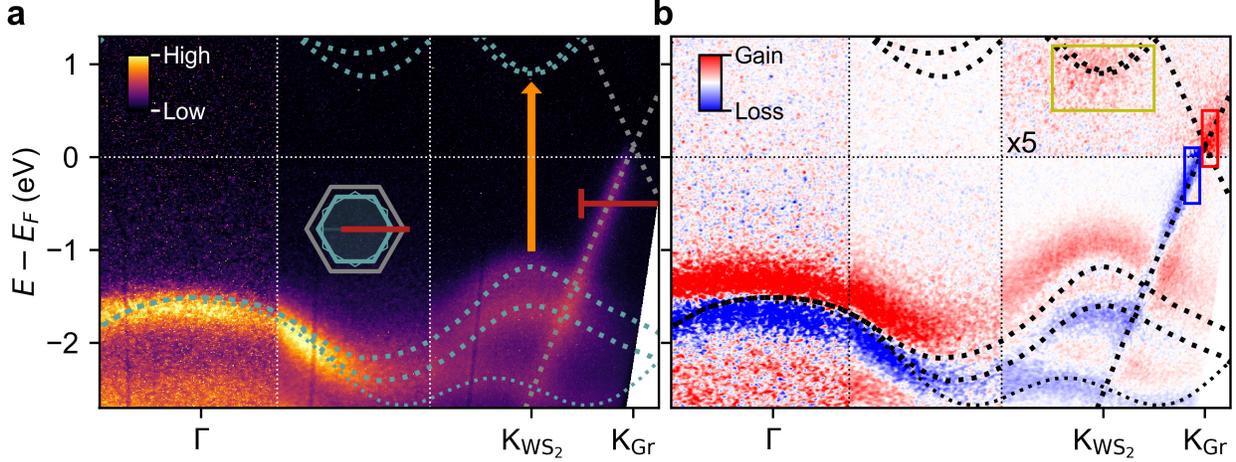


Figure 1: **trARPES data of WS₂-graphene heterostructure.** **a)** ARPES spectrum measured at negative pump-probe delay before the arrival of the pump pulse along the ΓK direction as indicated by the red line in the inset. The orange vertical arrow illustrates the excitation resonant to the A-exciton at $\hbar\omega_{\text{pump}} = 2.0$ eV. Gray and green dashed lines indicate the theory band structures for graphene¹⁸ and WS₂¹⁷, respectively, that were shifted in energy to match the observed band alignment. The thin dashed green line marks the band structure of WS₂ flakes with 30° rotation relative to the graphene layer. The horizontal red line covers the k range over which EDCs in Fig. 3b) are extracted. **b)** Pump-induced changes 250 fs after excitation at $\hbar\omega_{\text{pump}} = 2.0$ eV with a fluence of 1.5 mJ cm⁻². Red and blue indicate a gain and loss of photocurrent with respect to negative pump-probe delays, respectively. The upper right panel is multiplied with a factor of 5 for better visibility. Colored boxes indicate the area of integration for the pump-probe traces in Fig. 3a).

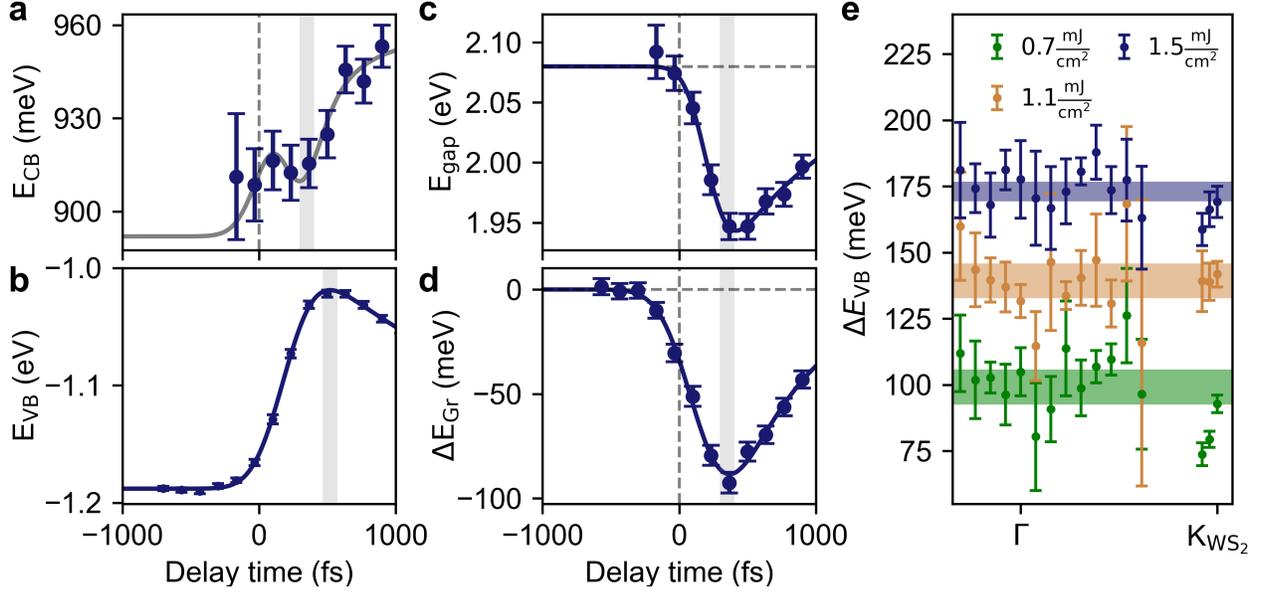


Figure 2: **trARPES data analysis.** **a)** Transient CB position. The gray line is a guide to the eye obtained by adding the transient band gap fit from **c)** to the fit of the VB position from **b)**. **b)** Transient band shift of the upper VB at the K point together with exponential decay fit. **c)** Transient band gap obtained by subtracting the data from **a)** and **b)** together with exponential decay fit. **d)** Graphene band shift together with exponential decay fit. Vertical grey lines in **a)**-**d)** mark the pump-probe delay where the VB shift at K reaches its maximum. **e)** k -dependent VB shifts for different excitation fluences for the pump-probe delay where the VB shift at K reaches its maximum. Horizontal lines represent momentum-averaged shifts. The line width reflects the standard deviation.

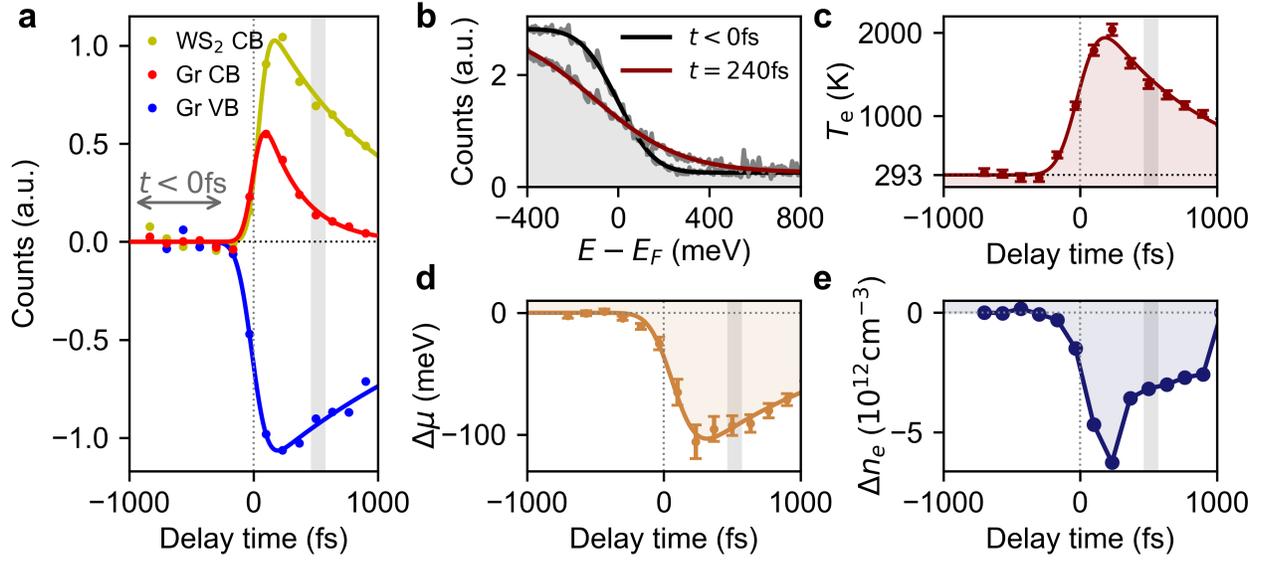


Figure 3: **Charge transfer dynamics.** **a)** Photocurrent integrated over the colored boxes from Fig. 1b). The grey arrow marks the integration range for the ARPES spectrum in Fig. 1a). **b)** Energy distribution curve showing the Fermi edge in the Dirac cone for two different pump-probe delays together with Fermi-Dirac fits. **c)** Electronic temperature in the Dirac cone as a function of pump-probe delay together with exponential decay fit. **d)** Chemical potential inside the graphene layer as a function of pump-probe delay together with exponential decay fit. **e)** Changes in carrier density in the graphene layer, calculated from the electronic temperature from c), the chemical potential from d) and the density of states. Vertical grey lines in a), c), d) and e) mark the pump-probe delay where the VB shift at K reaches its maximum.

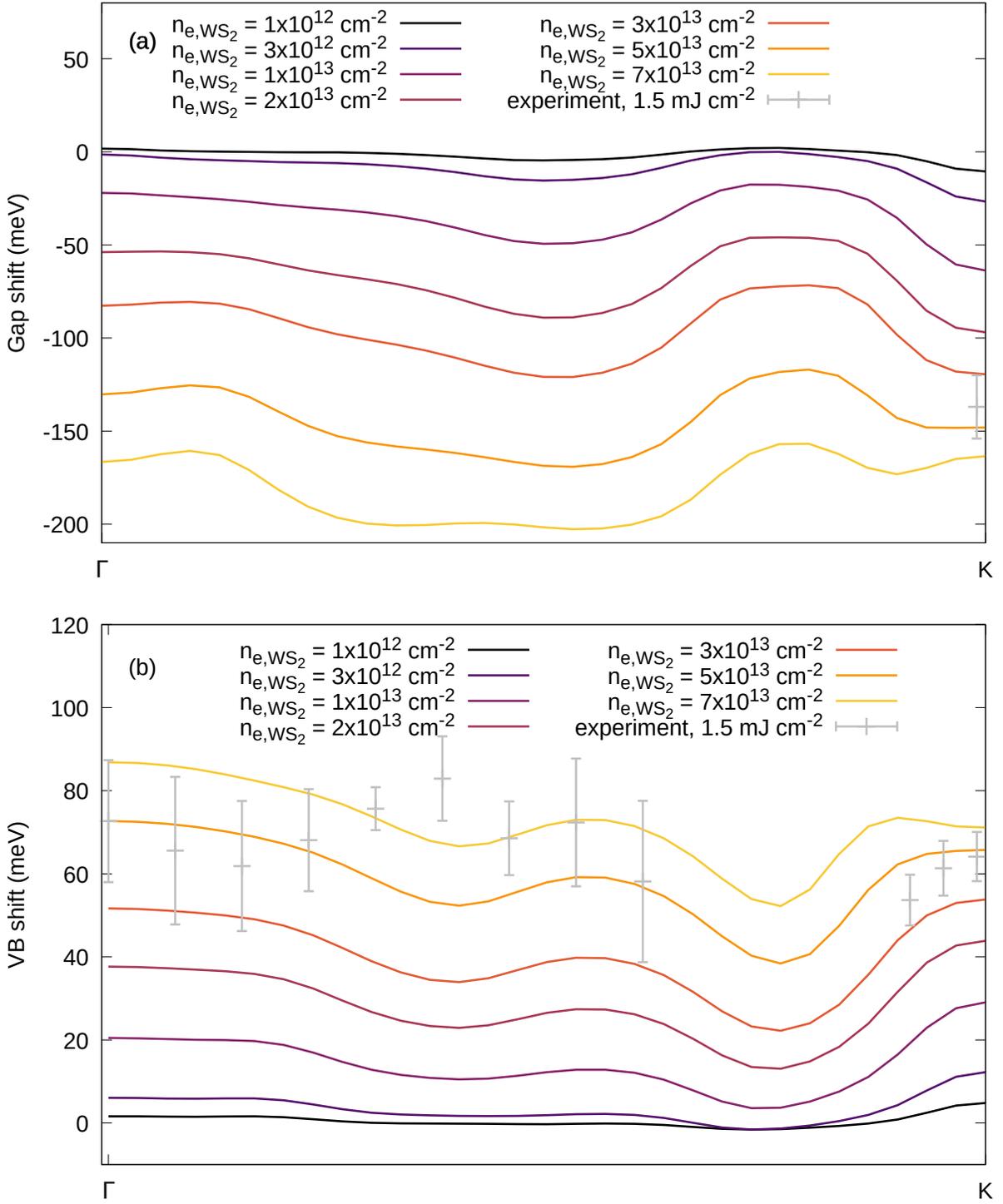


Figure 4: **Theory.** Calculated k-resolved transient band gap (a) and quasi-particle shifts of WS₂ VB (b) for different carrier densities for a carrier temperature of $T = 1500 \text{ K}$. The grey dots represent charging-shift-corrected experimental data points for a fluence of 1.5 mJ cm^{-2} .

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